



Abstract

The limiter of the invention uses as a diode a stacked gate thin film transistor (TFT) including a floating gate. When the TFT including a floating gate is used, the threshold voltage Vth may be corrected by controlling the amount of charge accumulated in the floating gate even in the case where there are variations in the threshold voltages Vth of the TFT.

By using a stacked gate transistor including a floating gate in a limiter, a threshold voltage Vth of the stacked gate transistor can be corrected by controlling the amount of charge accumulated in the floating gate of the stacked gate transistor even in the case where there are variations in the threshold voltage Vth of the stacked gate transistor.